ST 2SC3330

NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into five groups, R, O, Y, G and L, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package Weight approx. 0.19g

Absolute Maximum Ratings ($T_a = 25^{\circ}C$)

	Symbol	Value	Unit
Collector Base Voltage	V _{CBO}	60	V
Collector Emitter Voltage	V _{CEO}	50	V
Emitter Base Voltage	V _{EBO}	5	V
Collector Current	Ι _C	200	mA
Power Dissipation	P _{tot}	300	mW
Junction Temperature	Tj	150	°C
Storage Temperature Range	Ts	-55 to +150	°C







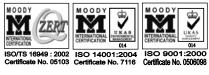
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Characteristics at $T_{amb}=25$ °C

	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain					
at V_{CE} =6V, I _C =1mA					
Current Gain Group R	h _{FE}	40	-	80	-
0	h _{FE}	70	-	140	-
Y	h _{FE}	120	-	240	-
G	h _{FE}	200	-	400	-
L	h _{FE}	350	-	700	-
Collector Base Breakdown Voltage					
at I _C =100μA	V _{(BR)CBO}	60	-	-	V
Collector Emitter Breakdown Voltage					
at I _C =10mA	V _{(BR)CEO}	50	-	-	V
Emitter Base Breakdown Voltage					
at I _E =10µA	V _{(BR)EBO}	5	-	-	V
Collector Cutoff Current					
at V_{CB} =40V	I _{CBO}	-	-	0.1	μA
Emitter Cutoff Current					
at V _{EB} =3V	I _{EBO}	-	-	0.1	μΑ
Collector Saturation Voltage					
at I _C =100mA, I _B =10mA	V _{CE(sat)}	-	0.15	0.3	V
Gain Bandwidth Product					
at V_{CE} =6V, I _C =10mA	f⊤	-	200	-	MHz
Output Capacitance					
at V _{CB} =6V, f=1MHz	C _{OB}	-	2.5	-	pF
Noise Figure					
at V_{CE} =6V, I _E =0.5mA					
f=1KHz, R_s =500 Ω	NF	-	4	-	dB







Dated : 07/12/2002